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**Automotive Engine Control IC** 

The 33810 is an eight channel output driver IC intended for automotive engine control applications. The IC consists of four integrated low-side drivers and four low-side gate pre-drivers. The low-side drivers are suitable for driving fuel injectors, solenoids, lamps, and relays. The four gate pre-drivers can function either as ignition IGBT gate pre-drivers or as general purpose MOSFET gate pre-drivers. This device is powered by SMARTMOS technology.

When configured as ignition IGBT gate pre-drivers, additional features are enabled such as spark duration, dwell time, and ignition coil current sense. When configured as a general purpose gate pre-driver (GPGD), the 33810 provides external MOSFETs with short-circuit protection, inductive flyback protection and diagnostics. The device is packaged in a 32 pin (0.65mm pitch) exposed pad SOIC.

#### **Features**

- Designed to operate over the range of 4.5 V ≤ VPWR ≤ 36 V
- Quad ignition IGBT or MOSFET gate pre-driver with parallel/SPI and/or PWM control
- Quad injector driver with parallel/SPI control
- Interfaces directly to MCU using 3.3 V/5.0 V SPI protocol
- · Injector driver current limit 4.5 A max.
- · Independent fault protection and diagnostics
- V<sub>PWR</sub> standby current 10 μA max.

# 33810

#### **ENGINE CONTROL**



#### **Applications**

- Automotive
- Motorcycle engine control unit (ECU) and small engine control
- PSI5 airbag system
- · Central gateway/in-vehicle networking
- Braking and stability control
- Gasoline engine management
- Hybrid electric vehicle (HEV) inverter controller

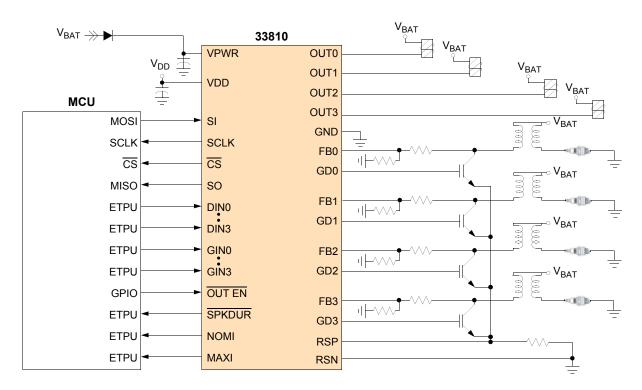


Figure 1. MC33810 Simplified Application Diagram





# **ORDERABLE PARTS**

This section describes the part numbers available to be purchased along with their differences. Valid orderable part numbers are provided on the web. To determine the orderable part numbers for this device, go to <a href="http://www.freescale.com">http://www.freescale.com</a> and perform a part number search for the following device numbers.

#### **Table 1. Orderable Part Variations**

Part Number	Notes	Temperature (T <sub>A</sub> )	Package
MCZ33810EK	(1)	-40 °C to 125 °C	32 SOICW-EP

#### Notes

1. To order parts in Tape & Reel, add the R2 suffix to the part number.



# INTERNAL BLOCK DIAGRAM

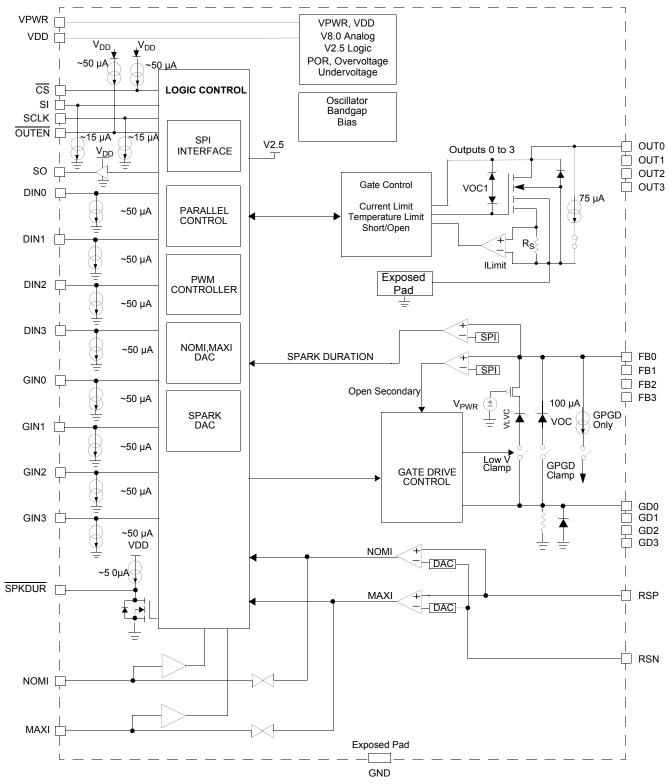


Figure 2. 33810 Simplified Internal Block Diagram



# **PIN CONNECTIONS**

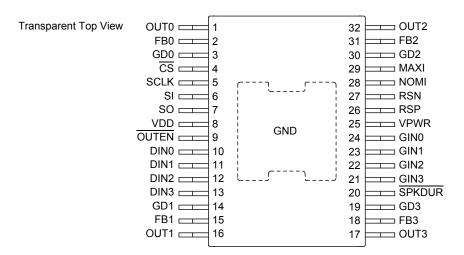


Figure 3. 33810 Pin Connections

A functional description of each pin can be found in the Functional Pin Description section beginning on page 14.

Table 2. 33810 Pin Definitions

Pin Number	Pin Name	Pin Function	Formal Name	Definition
1, 16, 32, 17	OUT0, OUT1, OUT2, OUT3	Output	Low-side Injector Driver Output	These pins are the Open drain low-side injector driver outputs.
2, 15, 31, 18	FB0, FB1, FB2, FB3	Input	Feedback Voltage Sense	In IGBT ignition gate pre-driver mode, these feedback inputs monitor the IGBT's collector voltage to provide the spark duration timer control signal.
3, 14, 30,19	GD0, GD1, GD2, GD3	Output	Gate Drive Output	IGBT/GPGD outputs are controlled by GIN0 - 3. Pull-up and pull-down current sources are used to provide a controlled slew rate to an external IGBT or MOSFET connected as a low-side driver.
4	CS	Input	Chip Select	The Chip Select input pin is an active low signal sent by the MCU to indicate the device is being addressed. This input requires CMOS logic levels and has an internal active pull-up current source.
5	SCLK	Input	Serial Clock Input	The SCLK input pin is used to clock the serial data on the SI and SO pins in and out while being addressed by the CS.
6	SI	Input	Serial Input Data	The SI input pin is used to receive serial data from the MCU.
7	SO	Output	Serial Output Data	The SO output pin is used to transmit serial data from the device to the MCU.
8	VDD	Input	Digital Logic Supply Voltage	The VDD input supply voltage determines the interface voltage levels between the device and the MCU, and is used to supply power to the Serial Out buffer (SO), SPKDUR buffer, MAXI, NOMI, and pull-up current source for the Chip Select (CS).
9	OUTEN	Input	Output Enable	The Output Enable pin (OUTEN) is an active low input. When the OUTEN pin is low, the device outputs are active. The outputs are disabled when OUTEN is high.
10, 11, 12, 13	DIN0,DIN1, DIN2,DIN3	Input	Driver Input 0, Driver Input 1, Driver Input 2, Driver Input 3	Active high input control for injector outputs OUT0 - 3. The parallel input data is logically ORed with the corresponding SPI input data register contents.
20	SPKDUR	Output	Spark Duration Output	This pin is the Spark Duration Output. This open drain output is low while feedback inputs FB0 - 3 are above the programmed spark detection threshold.
24, 23, 22, 21	GIN0,GIN1, GIN2,GIN3	Input	Gate Driver Input 0 Gate Driver Input 1 Gate Driver Input 2 Gate Driver Input 3	These pins are the active high input control for IGBT/GPGD outputs GD0 - 3. The parallel input data is logically ORed with the corresponding SPI input data register contents in GPGD mode only.
25	VPWR	Input	Analog Supply Voltage	VPWR is the main voltage input for all internal analog bias circuitry.



# Table 2. 33810 Pin Definitions (continued)

Pin Number	Pin Name	Pin Function	Formal Name	Definition
26	RSP	Input	Resistor Sense Positive	This pin is the Positive input of a current sense amplifier.
27	RSN	Input	Resistor Sense Negative	This pin is the Negative input of a current sense amplifier.
28	NOMI	Output	Nominal Ignition Coil Current	This pin is the Nominal Ignition Coil Current output flag. This output is asserted when the IGBT Collector-Emitter current exceeds the level selected by the DAC.
29	MAXI	Output	Maximum Ignition Coil Current	This pin is the Maximum Ignition Coil Current output flag. This output is asserted when the IGBT Collector-Emitter current exceeds the selected level of the DAC. This signal also latches off the gate pre-drive outputs when configured as a GPGD. The MAXI current level is determined by the voltage drop across an external sense resistor connected to pins RSP and RSN.
Exposed Pad (bottom of package)	GND	Ground	Ground	The exposed pad is the only ground reference for analog, digital and power ground connections. As such, it must be soldered directly to a low-impedance ground plane for both electrical and thermal considerations. For more information about this package, see application note AN2409 on the Freescale web site, <a href="https://www.freescale.com">www.freescale.com</a>



# **ELECTRICAL CHARACTERISTICS**

# **MAXIMUM RATINGS**

Table 3. Maximum Ratings

All voltages are with respect to ground unless otherwise noted.

Symbol	Ratings	Value	Unit	Notes
LECTRICAL RATINGS           VPWR         VPWR Supply Voltage         -1.5 to 45         V <sub>DC</sub> VDD         VDD Supply Voltage         -0.3 to 7.0         V <sub>DC</sub> V <sub>IL</sub> V <sub>IL</sub> GIN0 - GIN3, SPKDUR, NOMI, MAXI, RSP,RSN)         -0.3 to V <sub>DD</sub> V <sub>DC</sub> V <sub>FB</sub> IGBT/GPGD Drain Voltage (V <sub>FB0</sub> to V <sub>FB3</sub> )         -1.5 to 60         V <sub>DC</sub> V <sub>OUTX</sub> Injector Output Voltage (OUTx)         -1.5 to 60         V <sub>DC</sub> V <sub>GDx</sub> GPGD Output Voltage (GDx)         -0.3 to 10         V <sub>DC</sub> E <sub>CLAMP</sub> Output Clamp Energy (OUT0 to OUT3)(Single Pulse)         100         mJ           T <sub>JUNCTION</sub> = 150 °C, I <sub>OUT</sub> = 1.5 A         100         mJ           E <sub>CLAMP</sub> Output Clamp Energy (OUT0 to OUT3)(Continuous Pulse)         100         mJ           I <sub>OSSSS</sub> T <sub>JUNCTION</sub> = 125 °C, I <sub>OUT</sub> = 1.0 A (Max Injector frequency is 70 Hz)         100         mJ           I <sub>OSSSS</sub> Maximum Voltage for RSN and RSP inputs         -0.3 - V <sub>DD</sub> V <sub>DC</sub> -         Frequency of SPI Operation (V <sub>DD</sub> = 5.0 V)         6.0         MHz           V <sub>ESD1</sub> Human Body Model (HBM)         ±2000         V				
V <sub>PWR</sub>	VPWR Supply Voltage	-1.5 to 45	$V_{DC}$	(1)
$V_{DD}$	VDD Supply Voltage	-0.3 to 7.0	$V_{DC}$	(1)
	SPI Interface and Logic Input Voltage (CS, SI, SO, SCLK, OUTEN, DIN0 - DIN3, GIN0 - GIN3, SPKDUR, NOMI, MAXI, RSP,RSN)	-0.3 to V <sub>DD</sub>	V <sub>DC</sub>	
V <sub>FB</sub>	IGBT/GPGD Drain Voltage (V <sub>FB0</sub> to V <sub>FB3</sub> )	-1.5 to 60	$V_{DC}$	
V <sub>OUTX</sub>	Injector Output Voltage (OUTx)	-1.5 to 60	$V_{DC}$	
V <sub>GDx</sub>	GPGD Output Voltage (GDx)	-0.3 to 10	$V_{DC}$	
E <sub>CLAMP</sub>	, , , , ,	100	mJ	
E <sub>CLAMP</sub>		100	mJ	
I <sub>OSSSS</sub>	·	2.0	А	
V <sub>RSX</sub>	Maximum Voltage for RSN and RSP inputs	-0.3 - V <sub>DD</sub>	$V_{DC}$	
-	Frequency of SPI Operation (V <sub>DD</sub> = 5.0 V)	6.0	MHz	
V <sub>ESD1</sub> V <sub>ESD2</sub> V <sub>ESD3</sub>		±2000 ±200 ±750	V	(2), (3)

#### THERMAL RATINGS

T <sub>A</sub> T <sub>J</sub> T <sub>C</sub>	Operating Temperature Ambient Junction2 Case	-40 to 125 -40 to 150 -40 to 125	°C	
T <sub>STG</sub>	Storage Temperature	-55 to 150	°C	
P <sub>D</sub>	Power Dissipation (T <sub>A</sub> = 25 °C)	1.7	W	
T <sub>SOLDER</sub>	Peak Package Flow Temperature During Solder Mounting EW Suffix	245	°C	
R <sub>θJA</sub> R <sub>θJL</sub> R <sub>θJC</sub>	Thermal Resistance Junction-to-Ambient Junction- to-Lead Junction-to-Flag	75 8.0 1.2	°C/W	

#### Notes

- 1. Exceeding these limits may cause malfunction or permanent damage to the device.
- 2. ESD data available upon request.
- 3. ESD testing is performed in accordance with the Human Body Model (HBM) (AEC-Q100-002), the Machine Model (MM) (AEC-Q100-003), and the Charge Device Model (CDM), Robotic (AEC-Q100-011).



#### STATIC ELECTRICAL CHARACTERISTICS

#### **Table 4. Static Electrical Characteristics**

Characteristics noted under conditions of 3.0 V  $\leq$  V<sub>DD</sub>  $\leq$  5.5 V, 6.0 V  $\leq$  V<sub>PWR</sub>  $\leq$  32 V, -40 °C  $\leq$  T<sub>C</sub>  $\leq$  125 °C, and calibrated timers, unless otherwise noted. Typical values reflect the parameter's approx. average value with V<sub>PWR</sub> = 13 V, T<sub>A</sub> = 25 °C.

Symbol	Characteristic	Min	Тур	Max	Unit	Notes
POWER INPUT (V	(DD, VPWR)					
V <sub>PWR(FO)</sub>	Supply Voltage Fully Operational Full Parameter Specification	4.5 6.0	_ _	36 32	V	(4)
I <sub>VPWR(ON)</sub>	Supply Current All Outputs Disabled (Normal mode)	-	10.0	14.0	mA	
I <sub>VPWR(SS)</sub>	Sleep State Supply Current (Must have $V_{DD} \le 0.8 \text{ V}$ for Sleep state), $V_{PWR}$ = 32 V	-	15	30	μА	
V <sub>PWR(OV)</sub>	V <sub>PWR</sub> Overvoltage Shutdown Threshold Voltage	36.5	39	42	V	(5)
V <sub>PWR(OV-HYS)</sub>	V <sub>PWR</sub> Overvoltage Shutdown Hysteresis Voltage	0.5	1.5	3.0	V	
V <sub>PWR(UV)</sub>	V <sub>PWR</sub> Undervoltage Shutdown Threshold Voltage	3.0	4.0	4.4	V	(6)
V <sub>PWR(UV-HYS)</sub>	V <sub>PWR</sub> Undervoltage Shutdown Hysteresis Voltage	100	200	300	mV	
V <sub>PWR(LOV)</sub>	V <sub>PWR</sub> Low Operating Voltage (Low-voltage reported via the SPI)	5.3	_	8.99	V	(7)
$V_{DD}$	VDD Supply Voltage	3.0	_	5.5	V	
I <sub>VDD</sub>	VDD Supply Current Static condition and does not include V <sub>DD</sub> current out of device	_	-	1.0	mA	
V <sub>DD(UV)</sub>	VDD Supply Undervoltage (Sleep state) Threshold Voltage	0.8	2.5	2.8	V	(8)
	R OUTPUTS (OUT 0:3)		I.	I	I	· I
R <sub>DS (ON)</sub>	Drain-to-Source ON Resistance $I_{OUT} = 1.0 \text{ A, } T_J = 125 ^{\circ}\text{C, VPWR} = 13 \text{ V}$ $I_{OUT} = 1.0 \text{ A, } T_J = 25 ^{\circ}\text{C, VPWR} = 13 \text{ V}$ $I_{OUT} = 1.0 \text{ A, } T_J = -40 ^{\circ}\text{C, VPWR} = 13 \text{ V}$	- - -	- 0.2 -	0.3 - -	Ω	
I <sub>OUT(LIM)</sub>	Output Self Limiting Current	3.0	_	6.0	Α	
V <sub>OUT(FLT-TH)</sub>	Output Fault Detection Voltage Threshold Outputs Programmed OFF (Open Load) Outputs Programmed ON (Short to Battery)	2.0	2.5	3.0	V	(9)
I <sub>(OFF)OCO</sub>	Output OFF Open Load Detection Current  V <sub>DRAIN</sub> = 18 V, Outputs Programmed OFF  V <sub>DRAIN</sub> = 32 V, Outputs Programmed OFF (-40 °C)	40 40	75 75	115 115	μА	
I <sub>(ON)OCO</sub>	Output ON Open Load Detection Current Current less then specification value considered open	20	100	200	mA	
V <sub>OC1</sub>	Output Clamp Voltage 1 I <sub>D</sub> = 20 mA	48	53	58	V	

#### Notes

- 4. These parameters are guaranteed by design but not production tested. Fully operational means driver outputs toggle as expected with input toggling. SPI is guaranteed to be operational when  $V_{PWR} > 4.5 \text{ V}$ . SPI may not report correctly when  $V_{PWR} < 4.5 \text{ V}$ .
- 5. Overvoltage thresholds minimum and maximum include hysteresis.
- 6. Undervoltage thresholds minimum and maximum include hysteresis.
- 7. Device is functional provided T<sub>1</sub> is less than 150 °C. Some table parameters may be out of specification.
- 8. Device in Sleep state, returns from Sleep state with Power On Reset.
- 9. Output fault detection thresholds with outputs programmed OFF. Output fault detect thresholds are the same for output open and shorts.



#### Table 4. Static Electrical Characteristics (continued)

Characteristics noted under conditions of 3.0 V  $\leq$  V<sub>DD</sub>  $\leq$  5.5 V, 6.0 V  $\leq$  V<sub>PWR</sub>  $\leq$  32 V, -40 °C  $\leq$  T<sub>C</sub>  $\leq$  125 °C, and calibrated timers, unless otherwise noted. Typical values reflect the parameter's approx. average value with V<sub>PWR</sub> = 13 V, T<sub>A</sub> = 25 °C.

Symbol	Characteristic	Min	Тур	Max	Unit	Notes
INJECTOR DRIVE	R OUTPUTS (OUT 0:3) (Continued)					•
	Output Leakage Current  V <sub>DD</sub> = 5.0 V, V <sub>DRAIN</sub> = 24 V, Open Load Detection Current  Disabled	_	_	20		
I <sub>OUT(LKG)</sub>	$V_{DD}$ = 5.0 V, $V_{DRAIN}$ = $V_{OC}$ - 1.0 V, Open Load Detection Current Disabled	-	-	3000	μΑ	
	VDD = 0 V, V <sub>DRAIN</sub> = 24 V, Sleep State	_	_	10		
T <sub>LIM</sub>	Overtemperature Shutdown	155	-	185	°C	(10)
T <sub>LIM(HYS)</sub>	Overtemperature Shutdown Hysteresis	5.0	10	15	°C	(10)
IGNITION (IGBT)	GATE DRIVER PARAMETERS (GD 0:3 FB0:3)		•	•	•	•
V <sub>GS(ON)</sub> V <sub>GS(OFF)</sub>	Gate Driver Output Voltage $I_{GD}$ = 500 $\mu$ A $I_{GD}$ = -500 $\mu$ A	4.8 0.0	7.0 0.375	9.0 0.5	V	
R <sub>GS(PULLDOWN)</sub>	Sleep Mode Gate to Source Resistor	100	200	300	ΚΩ	
I <sub>FBX(LKG)</sub>	Sleep Mode FBx Pin Leakage Current VDD = 0 V, V <sub>FBx</sub> = 24 V,	-	_	1.0	μА	
I <sub>FBX(FLT-SNS)</sub>	Feedback Sense Current (FBx Input Current) FBx = 32 V. Outputs Programmed OFF	_	_	1.0	μА	

#### SOFT SHUTDOWN FUNCTION (VOLTAGES REFERENCED TO IGBT COLLECTOR)

Gate Drive Turn OFF Resistance

FBx = 32 V, Outputs Programmed OFF Gate Drive Source Current (1.0  $\leq$  V<sub>GD</sub>  $\leq$  3.0)

V <sub>LVC</sub>	Low Voltage Flyback Clamp Driver Command OFF, Soft Shutdown Enabled, GDx = 2.0 V	V <sub>PWR</sub> +9.0	V <sub>PWR</sub> +11	V <sub>PWR</sub> +13	V	
V <sub>TH-RISE</sub>	Spark Duration Comparator Threshold (referenced to IC Ground Tab) Rising Edge Relative to VPWR	18	21	24	V	
V <sub>TH-FALL</sub>	Spark Duration Comparator Threshold (referenced to IC Ground Tab) Falling Edge Relative to V <sub>PWR</sub> , Default = 5.5 V assuming ideal external 10:1 voltage divider. Voltage measured at high end of divider, not at pin. Tolerance of divider not included.	1.2 4.9 7.4 9.9	2.75 5.5 8.2 11.00	3.6 6.1 9.1 12.1	٧	(11)
V <sub>TH-RISE</sub>	Open Secondary Comparator Threshold (referenced from primary to rising edge relative to GND). No hysteresis with 10:1 voltage divider.	11.5	-	15.5	V	

650

500

780

950

1000

μΑ

Ω

#### Notes

**I**GATEDRIVE

R<sub>DS(ON)</sub>

- 10. This parameter is guaranteed by design but not production tested.
- Assuming ideal external 10:1 Voltage Divider. Tolerance of 10:1 Voltage Divider is not included. Voltage is measured on the high end of the divider - not at the pin. 10:1 N.3.A 10:1 Voltage Divider is produced using two resistors with a 9:1 resistance ratio by the basic formula:

$$\frac{\text{VOUT}}{\text{VIN}} = \frac{\text{R1}}{\text{R1} + \text{R2}} \quad \text{Where R2} = 9\text{XR1}$$



# Table 4. Static Electrical Characteristics (continued)

Characteristics noted under conditions of 3.0 V  $\leq$  V<sub>DD</sub>  $\leq$  5.5 V, 6.0 V  $\leq$  V<sub>PWR</sub>  $\leq$  32 V, -40 °C  $\leq$  T<sub>C</sub>  $\leq$  125 °C, and calibrated timers, unless otherwise noted. Typical values reflect the parameter's approx. average value with V<sub>PWR</sub> = 13 V, T<sub>A</sub> = 25 °C.

Symbol	Characteristic	Min	Тур	Max	Unit	Notes
CURRENT SENSE	COMPARATOR (RSP, RSN)	l l		1		1
NOMI <sub>TRIPTA</sub>	NOMI Trip Threshold Accuracy - Steady State Condition 3.0 A across 0.02 $\Omega$ (RSP - RSN = 60 mV) 10.75 A across 0.04 $\Omega$ (RSP - RSN = 430 mV)	-10	-	10	%	
MAXI <sub>TRIPTA</sub>	MAXI Trip Threshold Accuracy - Steady State Condition 6.0 A across 0.02 $\Omega$ (RSP - RSN = 120 mV) 21 A across 0.04 $\Omega$ (RSP - RSN = 840 mV)	- -7.5	<u>-</u>	7.5 –	%	
MAXI <sub>TRIPOD</sub>	MAXI Trip Point During Overlapping Dwell	-35	-	+35	%	
I <sub>BIASRSX</sub>	Input Bias Current RSP and RSN	-50	_	50	μA	
NOMI <sub>HYS</sub> MAXII <sub>HYS</sub>	Comparator Hysteresis Voltage NOMI MAXI	40 40	_ _	70 70	% of VT	
VCMVR <sub>CMVR</sub>	Input Voltage Range (Maximum voltage between RSN and RSP)	0.0	_	2.0	V	(12)
VGND <sub>OVR</sub>	Ground Offset Voltage Range Maximum offset between RSN pin and IC Ground (Exposed Pad)	-0.3	_	0.3	V	(12)
GENERAL PURPO	OSE GATE PRE-DRIVER PARAMETERS (GD0:3)					•
I <sub>GD</sub>	Gate Drive Sink and Source Current	1.0	2.0	5.0	mA	
V <sub>GS(ON)</sub> V <sub>GS(OFF)</sub>	Gate Drive Output Voltage  I <sub>GD</sub> = 1.0 mA  I <sub>GD</sub> = -1.0 mA	4.8 0.0	7.0 0.2	9.0 0.5	V	
V <sub>DS(FLT-TH)</sub>	Short to Battery Fault Detection Voltage Threshold  V <sub>DD</sub> = 5.0 V, Outputs Programmed ON  Programmable from 0.5 V to 3.0 V in 0.5 V increments. ( <u>Table 15</u> )	-35%	-	+35%	V	
V <sub>DS(FLT-TH)</sub>	Open Fault Detection Voltage Threshold (referenced to IC ground tab) $V_{DD}$ = 5.0 V, Outputs Programmed OFF	2.0	2.5	3.0	V	
I <sub>FBX(FLT-SNS)</sub>	Output OFF Open Load Detection Current FBx = 18 V, Outputs Programmed OFF	50	75	120	μА	
V <sub>oc</sub>	Output Clamp Voltage Driver Command OFF, Clamp Enabled, V <sub>GATE</sub> = 2.0 V	48	53	58	٧	
DIGITAL INTERFA	ACE	<u> </u>		<del> </del>		
V <sub>IH</sub>	Input Logic High-voltage Thresholds	0.7 x V <sub>DD</sub>	_	V <sub>DD</sub> + 0.3	V	
V <sub>IL</sub>	Input Logic Low-voltage Thresholds	GND - 0.3	_	0.2 x V <sub>DD</sub>	V	
V <sub>HYS</sub>	Input Logic Voltage Hysteresis	100	_	400	mV	
C <sub>IN</sub>	Input Logic Capacitance	_	-	20	pF	
I <sub>LOGIC_</sub> ss	Sleep Mode Input Logic Current VDD = 0 V	-10	-	10	μΑ	
I <sub>LOGIC_PD</sub>	Input Logic Pull-down Current 0.8 to 5.0 V (DIN <sub>X</sub> and GIN <sub>X</sub> )	30	50	100	μА	
I <sub>SI_PD</sub>	Input Logic Pull-down Current 0.8 to 5.0 V (SI)	5.0	15	25	μА	
l <del>outen</del> _pu	Input Logic Pull-up Current on OUTEN OUTEN = 0.0 V, V <sub>DD</sub> = 5.0 V	-30	-50	-100	μА	

# Notes

12. This parameter is guaranteed by design, but not production tested.



# Table 4. Static Electrical Characteristics (continued)

Characteristics noted under conditions of 3.0 V  $\leq$  V<sub>DD</sub>  $\leq$  5.5 V, 6.0 V  $\leq$  V<sub>PWR</sub>  $\leq$  32 V, -40 °C  $\leq$  T<sub>C</sub>  $\leq$  125 °C, and calibrated timers, unless otherwise noted. Typical values reflect the parameter's approx. average value with V<sub>PWR</sub> = 13 V, T<sub>A</sub> = 25 °C.

Symbol	Characteristic	Min	Тур	Max	Unit	Notes
DIGITAL INTERF	ACE (CONTINUED)	-			ı	<u>.l</u>
I <sub>OUTEN(LKG)</sub>	OUTEN Leakage Current to V <sub>DD</sub> OUTEN = 5.0 V, V <sub>DD</sub> = 0 V	-	-	50	μА	
I <sub>SCLK</sub>	SCLK Pull-down Current V <sub>SCLK</sub> = V <sub>DD</sub>	5.0	15	25	μА	
I <sub>TRISO</sub>	Tri-state SO Output 0 to 5.0 V	-10	-	10	μА	
I <sub>CS</sub>	CS Input Current CS = V <sub>DD</sub>	-50	_	50	μА	
I <del>CS</del> _PU	CS Pull-up Current CS = 0 V	-30	-50	-100	μА	
I <del>CS</del> (LKG)	CS Leakage Current to V <sub>DD</sub> CS = 5.0 V, V <sub>DD</sub> = 0 V	-	-	50	μА	
C <sub>SO</sub>	SO Input Capacitance in Tri-state Mode	_	20	-	pF	
V <sub>SO_HIGH</sub>	SO High State Output Voltage I <sub>SO-HIGH</sub> = -1.0 mA	V <sub>DD</sub> - 0.4	-	-	V	
V <sub>SO_LOW</sub>	SO Low State Output Voltage I <sub>SO-LOW</sub> = 1.0 mA	-	-	0.4	V	
I <sub>PD</sub>	NOMI, MAXI in V10 Mode Pull-down Current NOMI, MAXI = 0.8 V, V <sub>DD</sub> = 5.0 V	30	70	100	μА	
V <sub>SPKDUR_LO</sub>	SPKDUR Output Voltage ISPKDUR = 1.0 mA	-	-	0.4	V	
ISPKDUR_PV	Output Pull-up Current for SPKDUR	30	50	100	μА	
$V_{I\_HIGH}$	NOMI, MAXI High State Output Voltage  I <sub>NOMI-HIGH</sub> = -1.0 mA  I <sub>MAXI-HIGH</sub> = -1.0 mA	V <sub>DD</sub> - 0.4	-	_	٧	
$V_{I\_LOW}$	NOMI, MAXI Low State Output Voltage I <sub>NOMI-LOW</sub> = 250 μA I <sub>MAXI-LOW</sub> = 250 μA	-	-	0.4	V	



# **DYNAMIC ELECTRICAL CHARACTERISTICS**

# **Table 5. Dynamic Electrical Characteristics**

Characteristics noted under conditions of 3.0 V  $\leq$  V<sub>DD</sub>  $\leq$  5.5 V, 6.0 V  $\leq$  V<sub>PWR</sub>  $\leq$  32 V, -40 °C  $\leq$  T<sub>C</sub>  $\leq$  125 °C, and calibrated timers, unless otherwise noted. Where applicable, typical values reflect the parameter's approximate average value with V<sub>PWR</sub> = 13 V, T<sub>A</sub> = 25 °C.

Symbol	Characteristic	Min	Тур	Max	Unit	Notes
WER INPUT	-					I
t <sub>UV</sub>	Required Low State Duration on $V_{PWR}$ for Undervoltage Detect $V_{PWR} \! \leq \! 0.2 \; V$	1.0	_	_	μS	
t <sub>RESET</sub>	Required Low State Duration on $V_{DD}$ for Power On Reset $V_{DD} \le 0.2 \text{ V}$	1.0	_	_	μS	
ECTOR DRIVI	ERS		•			1
t <sub>SC</sub>	Output ON Current Limit Fault Filter Timer (Short to Battery Fault)	30	60	90	μs	
t <sub>(ON)OC</sub>	Output ON Open Circuit Fault Filter Timer	3.0	7.5	12	ms	
t <sub>REF</sub>	Output Retry Timer	-	10	15	ms	
t <sub>(OFF)OC</sub>	Output OFF Open Circuit Fault Filter Timer	100	_	400	μs	
t <sub>SR(RISE)</sub>	Output Slew Rate (No faster than 1.5 $\mu$ s from OFF to ON and ON to OFF) $R_{LOAD}$ = 14 $\Omega$ , $V_{LOAD}$ = 14 V	1.0	5.0	10	V/μs	
t <sub>SR(FALL)</sub>	Output Slew Rate $R_{LOAD}$ = 14 $\Omega$ , $V_{LOAD}$ = 14 $V$	1.0	5.0	10	V/μs	
t <sub>PHL</sub>	Propagation Delay (Input Rising Edge OR $\overline{\text{CS}}$ to Output Falling Edge) Input at 50%V <sub>DD</sub> to Output voltage 90% of V <sub>LOAD</sub>	_	1.0	5.0	μs	
t <sub>PLH</sub>	Propagation Delay (Input Falling Edge OR CS to Output Rising Edge) Input at 50%V <sub>DD</sub> to Output voltage 10% of V <sub>LOAD</sub>	_	1.0	5.0	μs	
IITION & GEN	ERAL PURPOSE GATE PRE-DRIVER PARAMETERS		•			
t <sub>PLH</sub>	Propagation Delay (GINx Input Rising Edge OR $\overline{\text{CS}}$ to Output Rising Edge) Input at 50%V $_{\text{DD}}$ to Output voltage 10% of V $_{\text{GS}(\text{ON})}$	-	0.2	1.0	μs	
t <sub>PHL</sub>	Propagation Delay (Input Falling Edge OR $\overline{\text{CS}}$ to Output Falling Edge) Input at 50%V <sub>DD</sub> to Output voltage 90% of V <sub>GS(ON)</sub>	-	0.2	1.0	μs	
IITION PARAM	METERS					
	Open Secondary Fault Timer Accuracy (uncalibrated)	-35	_	35	%	
	Maximum Dwell Timer Accuracy (uncalibrated)	-35	-	35	%	
	End of Spark Filter Accuracy (uncalibrated)	-35	_	35	%	(13)

# Notes

13. This parameter is guaranteed by design, however, it is not production tested.



# Table 5. Dynamic Electrical Characteristics (continued)

Characteristics noted under conditions of 3.0 V  $\leq$  V<sub>DD</sub>  $\leq$  5.5 V, 6.0 V  $\leq$  V<sub>PWR</sub>  $\leq$  32 V, -40 °C  $\leq$  T<sub>C</sub>  $\leq$  125 °C, and calibrated timers, unless otherwise noted. Where applicable, typical values reflect the parameter's approximate average value with V<sub>PWR</sub> = 13 V, T<sub>A</sub> = 25 °C.

Symbol	Characteristic	Min	Тур	Max	Unit	Notes
ENERAL PURP	OSE GATE PRE-DRIVER PARAMETERS					.1
V <sub>DS(FLT-TH)</sub>	Short to Battery Fault Detection Filter Timer Accuracy $V_{DD}$ = High, Outputs Programmed ON Programmable from 30 $\mu$ s to 960 $\mu$ s in replicating increments Tolerance of timer after using calibration command Tolerance of timer before using calibration command	-10 -35	-	+10 +35	%	
t <sub>(OFF)</sub> OC	Output OFF Open Circuit Fault Filter Timer  V <sub>DD</sub> = 5.0 V, Outputs OFF  Tolerance of timer before using calibration command	100	-	400	μs	
$PWM_{FREQ}$	PWM Frequency 10 Hz to 1.28 kHz Tolerance After Using Calibration Command PWM Frequency 10 Hz to 1.28 kHz Tolerance Before Using	-10%	-	10%		
	Calibration Command	-35%	-	35%		
GD <sub>SHRT_DC</sub>	Gate Driver Short Fault Duty Cycle	-	1.0	3.0	%	
PI DIGITAL INTI	ERFACE TIMING (14)					
t <sub>LEAD</sub>	Falling Edge of CS to Rising Edge of SCLK Required Setup Time	100	-	-	ns	
t <sub>LAG</sub>	Falling Edge of SCLK to Rising Edge of CS Required Setup Time	50	-	-	ns	
t <sub>SI(SU)</sub>	SI to Rising Edge of SCLK Required Setup Time	16	_	-	ns	
t <sub>SI(HOLD)</sub>	Rising Edge of SCLK to SI Required Hold Time	20	_	-	ns	
t <sub>R(SI)</sub>	SI, CS, SCLK Signal Rise Time	_	5.0	_	ns	(15)
t <sub>F(SI)</sub>	SI, CS, SCLK Signal Fall Time	_	5.0	_	ns	(16)
t <sub>SO(EN)</sub>	Time from Falling Edge of CS Low-impedance	_	-	55	ns	(17)
t <sub>SO(DIS)</sub>	Time from Rising Edge of CS to SO High-impedance	_	-	55	ns	(18)
t <sub>VALID</sub>	Time from Falling Edge of SCLK to SO Data Valid	_	25	55	ns	(19)
t <sub>STR</sub>	Sequential Transfer Rate Time required between data transfers	1.0	-	-	μs	
IGITAL INTERF	ACE					
t <sub>TIMER</sub>	Calibrated Timer Accuracy	_	_	10	%	
t <sub>TIMER</sub>	Un-calibrated Timer Accuracy	_	_	35	%	

#### Notes

- 14. These parameters are guaranteed by design. Production test equipment uses 1.0 MHz, 5.0 V SPI interface.
- 15. This parameter is guaranteed by design, however, it is not production tested.
- 16. Rise and Fall time of incoming SI,  $\overline{\text{CS}}$  and SCLK signals suggested for design consideration to prevent the occurrence of double pulsing.
- 17. Time required for valid output status data to be available on SO pin.
- 18. Time required for output states data to be terminated at SO pin.
- 19. Time required to obtain valid data out from SO following the fall of SCLK with 200 pF load.



# **TIMING DIAGRAMS**

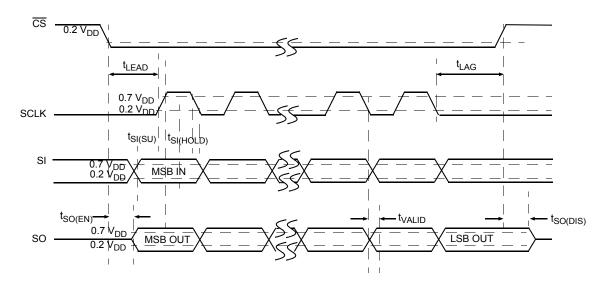


Figure 4. SPI Timing Diagram



#### **FUNCTIONAL DESCRIPTION**

#### **FUNCTIONAL PIN DESCRIPTION**

#### **ANALOG SUPPLY VOLTAGE (VPWR)**

The VPWR pin is the battery input to the 33810. The VPWR pin requires external reverse battery and transient protection. All IC analog current and internal logic current is provided from the VPWR pin. With  $V_{DD}$  applied to the IC, the application of VPWR performs a POR.

# **DIGITAL LOGIC SUPPLY VOLTAGE (VDD)**

The VDD input pin is used to determine communication logic levels between the microprocessor and the 33810. Current from VDD is used to drive SO output and the pull-up current for  $\overline{\text{CS}}$ .  $V_{\text{DD}}$  must be applied for Normal mode operation. Removing  $V_{\text{DD}}$  from the IC places the device in Sleep mode. With  $V_{\text{PWR}}$  applied to the IC, the application of  $V_{\text{DD}}$  performs a POR.

# **GROUND (GND)**

The bottom pad or FLAG provides the only ground connection for the IC. The  $V_{PWR}$  and  $V_{DD}$  supplies are both referenced to the GND pad. The GND pad is used for both de-coupling the power supplies as well as power ground for the output drivers. Although the silicon die is epoxy attached to the top side of the pad, the pad must be grounded for proper electrical operation.

#### **SERIAL CLOCK INPUT (SCLK)**

The system clock (SCLK) pin clocks the internal shift register of the 33810. The SI data is latched into the input shift register on the rising edge of SCLK signal. The <u>SO</u> pin shifts status bits out on the falling edge of SCLK. The SO data is available for the MCU to read on the rising edge of SCLK. With <u>CS</u> in a logic high state, signals on the SCLK and SI pins are ignored and the SO pin is tri-state.

# CHIP SELECT (CS)

The system MCU selects the 33810 to receive communication using the chip select  $(\overline{CS})$  pin. With the  $\overline{CS}$  in a logic low state, command words may be sent to the 33810 via the serial input (SI) pin, and status information is received by the MCU via the serial output (SO) pin. The falling edge of  $\overline{CS}$  enables the SO output and transfers status information into the SO buffer.

Rising edge of the  $\overline{\text{CS}}$  initiates the following operation:

Disables the SO driver (high-impedance)

Activates the received command word, allowing the 33810 to activate/deactivate output drivers.

To avoid any spurious data, it is essential the high-to-low and low-to-high transitions of the  $\overline{CS}$  signal occur only when SCLK is in a logic low state. Internal to the 33810 device is an active pull-up to  $V_{DD}$  on  $\overline{CS}$ .

# **SERIAL INPUT DATA (SI)**

The SI pin is used for serial instruction data input. SI information is latched into the input register on the rising edge of SCLK. A logic high state present on SI programs a logic [1] in the command word on the rising edge of the CS signal. To program a complete word, 16 bits of information or multiples of eight there of must be entered into the device.

### **SERIAL OUTPUT DATA (SO)**

The SO pin is the output from the shift register. The SO pin remains tri-stated until the  $\overline{CS}$  pin transitions to a logic <u>low</u> state. All normal operating drivers are reported as a logic [0], all faulted drivers are reported as a logic [1]. The negative transition of  $\overline{CS}$  enables the SO driver.

The SI/SO shifting of the data follows a first-in-first-out protocol, with both input and output words transferring the most significant bit (MSB) first.

# **OUTPUT ENABLE (OUTEN)**

The OUTEN pin is an active low input. When the OUTEN pin is low, all the device outputs are active. The outputs are all disabled when OUTEN pin is high. SPI and parallel communications are still active in either state of OUTEN.

# FEEDBACK VOLTAGE SENSOR (FB0-FB3)

The FBx pin has multiple functions for control and diagnostics of the external MOSFET/IGBT ignition gate driver. In Ignition (IGBT) mode, the feedback inputs monitor the IGBT's collector voltage to provide the Spark Duration Timer control signal. The Spark Duration Timer monitors this input to determine if the secondary clamp function should be activated. In secondary clamp mode, the IGBT's collector voltage is internally clamped to V<sub>PWR</sub> +11 V.



In the GPGD mode, this input monitors the drain of an external MOSFET to provide short-circuit and open circuit detection by monitoring the MOSFET's drain to source voltage. The filter timer and threshold voltage are easily programmed through SPI (See <u>Table 21</u> and <u>Table 22</u> for SPI messages). In GPGD mode the FBx pin also provides a drain to gate clamp for fast turn OFF of inductive loads and external MOSFET protection.

### **GATE DRIVER OUTPUT (GD0-GD3)**

The  $GD_X$  pins are the gate drive outputs for an external MOSFET or IGBT. Internal to the device is a Gate to Source resistor designed to hold the external device in the OFF state while the device is in the POR or Sleep state.

#### **LOW-SIDE INJECTOR DRIVER OUTPUT (OUT0 - OUT3)**

OUT0 - OUT3 are the open drain low-side (Injector) driver outputs. The drain voltage is actively clamped during turn OFF of inductive loads. These outputs can be connected in parallel for higher current loads provided the turn OFF energy rating is not exceeded.

#### **RESISTOR SENSE POSITIVE (RSP)**

Resistor Sense Positive - Positive input of a current sense amplifier. The ignition coil current is monitored by sensing the voltage across an external resistor connected between RSP and RSN. The output of the current sense amplifier feeds the inputs of the NOMI and MAXI comparators.

Note: RSN and RSP must be grounded in V10 mode.

#### **RESISTOR SENSE NEGATIVE (RSN)**

Resistor Sense Negative - Negative input of a current sense amplifier. The ignition coil current is monitored by sensing the voltage across an external resistor connected to RSP and RSN. The output of the current sense amplifier feeds the inputs of the NOMI and MAXI comparators.

Note: RSN and RSP must be grounded in V10 mode.

# NOMINAL IGNITION COIL CURRENT (NOMI)

Nominal ignition coil current output flag. This output is asserted when the output current exceeds the level selected by the DAC. NOMI can be configured as an input pin for V10 mode applications where the gate drive needs to be latched off by another device's MAXI current sense amplifier output. The NOMI input latches off gate drivers 5 and 6 when configured as a V10 mode ignition gate driver See Figure 11.

#### SPARK DURATION OUTPUT (SPKDUR)

SPKDUR is the Spark Duration output. This open drain output is low while feedback inputs FB0 through FB3 are above the programmed Spark Detection Threshold. This output indicates an ignition flyback event. Each feedback input (FB0 - FB3) is logically ORed to drive the SPKDUR output. There is a 50 µA pull up current source connected internally to the SPKDUR pin.

#### **MAXIMUM IGNITION COIL CURRENT (MAXI)**

Maximum ignition coil current output flag. This output is asserted when the output ignition coil current exceeds the selected level of the DAC. This signal also latches off the gate drive outputs when configured as an ignition gate driver. The MAXI current level is determined by the voltage drop across an external sense resistor connected to pins RSP and RSN.

MAXI can be configured as an input pin for V10 applications where the gate drive needs to be latched off by another devices MAXI current sense amplifier output. The MAXI input latches off gate drivers 7 and 8 when configured as ignition gate drive outputs (IGBTs) See Figure 11.

#### DRIVER INPUT (DIN0-DIN3), GATE DRIVER INPUT (GIN0-GIN3)

Parallel input pins for OUT0-OUT3 low-side drivers and GD0-GD3 gate drivers. Each parallel input control pin is active high and has an internal pull-down current sink. The parallel input data is logically ORed with the corresponding SPI input data register contents, except for the Ignition mode IGBT drivers. They are only controlled by the parallel inputs GIN0-GIN3. In GPGD mode, GIN0-GIN3 are logically ORed with SPI input data. All outputs are disabled when the OUTEN pin is high, regardless of the state of the command inputs.



#### **FUNCTIONAL INTERNAL BLOCK DESCRIPTION**

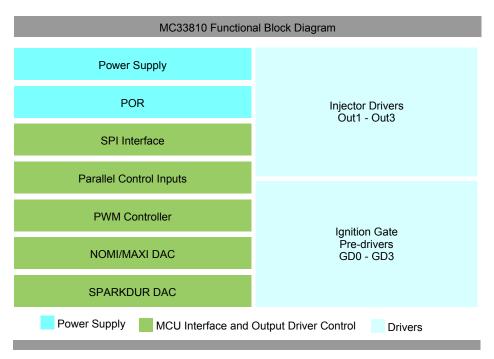


Figure 5. Functional Internal Block Diagram

#### **POWER SUPPLY/POR**

The 33810 is designed to operate from 4.5 V to 36 V on the VPWR pin. The VPWR pin supplies power to all internal regulators, analog, and logic circuit blocks. The  $V_{DD}$  supply is used for setting communication threshold levels and supplying power to the SO driver. This IC architecture provides a low quiescent current Sleep mode. Applying  $V_{PWR}$  and  $V_{DD}$  to the device generates a Power On Reset (POR) and place the device in the Normal state. The Power On Reset circuit incorporates a timer to prevent high frequency transients from causing a POR.

#### MCU INTERFACE AND OUTPUT CONTROL

This component provides parallel input pins for OUT0-OUT3 low-side drivers and GD0-GD3 gate drivers. Each parallel input control pin is active high and has an internal pull-down current sink. The parallel input data is logically ORed with the corresponding SPI input data register contents. All outputs are disabled when the OUTEN pin is high, regardless of the state of the command inputs.

#### **INJECTOR DRIVERS: OUT0 - OUT3**

These pins are the open drain low-side (Injector) driver outputs. The drain voltage is actively clamped during turn OFF of inductive loads. These outputs can be connected in parallel for higher current loads, provided the turn OFF energy rating is not exceeded.

#### **IGNITION GATE PRE-DRIVERS: GD0 – GD3**

These pins are the gate drive outputs for an external MOSFET or IGBT. Internal to the device is a Gate to Source resistor designed to hold the external device in the OFF state while the device is in the POR or Sleep state.



#### **FUNCTIONAL DEVICE OPERATION**

#### **MODES OF OPERATION**

#### **POWER SUPPLY**

The 33810 is designed to operate from 4.5 V to 36 V on the VPWR pin. The VPWR pin supplies power to all internal regulators, analog and logic circuit blocks. The  $V_{DD}$  supply is used for setting communication threshold levels and supplying power to the SO driver. This IC architecture provides flexible microprocessor interfacing and low quiescent current Sleep mode.

# **POWER ON RESET (POR)**

Applying V<sub>PWR</sub> and V<sub>DD</sub> to the device generates a Power On Reset (POR) and place the device in the Normal State. The Power On Reset circuit incorporates a filter to prevent high frequency transients from causing a POR.

All outputs are disabled when the OUTEN input pin is high regardless of the SPI control registers or the logic level on the parallel input pins. With the OUTEN pin high, SPI messages may be sent and received by the device. Upon enabling the device (OUTEN low), outputs are activated based on the state of the command register or parallel input.

**VPWR VDD OUTEN OUTPUTS STATE** L L Х OFF Power Off ı Н Х OFF POR Н L Х OFF Sleep Х OFF POR Н OFF POR Н X Χ OFF ı Sleep Н Н 1 Active Normal Н Н Н OFF Normal

**Table 6. Operational States** 

# SLEEP STATE

Sleep state is entered when the  $V_{DD}$  supply voltage is removed from the VDD pin. In Sleep state, all outputs are OFF. Applying  $V_{DD}$  forces the device to exit the Sleep state and generates a POR.

#### **NORMAL STATE**

The default Normal state is entered when power is applied to the VPWR and VDD pins. Control register settings from a Power On Reset (POR) are as follows:

- · All outputs OFF
- IGNITION gate driver mode enabled (IGBT Ignition mode).
- · PWM frequency and duty cycle control disabled.
- OFF state open load detection enabled (LSD)
- MAXI dac set to 14 A, NOMI DAC set to 5.5 A
- Spark detect level VIL DAC set to V<sub>PWR</sub> +5.5 V
- Open secondary timer set to 100 μs
- · Dwell timer set 32 ms
- Soft shutdown disabled
- Low-voltage flyback clamp disabled
- Dwell overlap MAXI offset disabled



#### **MODES OF OPERATION**

In Normal state, the 33810 gate driver has three modes of operation, Ignition mode, GPGD mode and V10 mode. The operating mode of each gate driver may be set individually and is programmed using the Mode Select command.

#### **MODE SELECT COMMAND**

The Mode Select command is used to set the operating mode for the GDx gate driver outputs, over/undervoltage operation and to enable V10 mode and the PWM generators. The Mode Select command programmable features are listed below.

- Ignition/GPGD mode select (gate drivers)
- V10 mode enable
- Over/Undervoltage operation for all drivers
- · GPGD PWM controller enable

#### **IGNITION/GPGD MODE SELECT**

The Ignition/GPGD mode select bits determine independently, the operating mode of each of the GDx gate driver outputs. Bits 8, 9, 10, 11 correspond to GD0, GD1, GD2, and GD3 respectively. Setting the bit to a logic 0 sets the GDx driver to the Ignition mode. Setting the bit to a logic [1] commands the GDX driver to the GPGD mode and disables the ignition features for that particular gate driver (except the MAXI current shutdown feature). Further information on GDx gate driver in Ignition mode and GPGD mode is provided later in this section of the data sheet.

#### **V10 MODE ENABLE BIT**

The V10 Enable bit allows the user to configure the device for 10 cylinder applications. When the V10 mode is enabled, the device configures the NOMI pin and MAXI pin as digital inputs rather than outputs. The new MAXI input pin receives the MAXI shutdown signal for GD0 and GD2 and the new NOMI input pin receives the MAXI shutdown signal for GD1 and GD3. Further information on V10 mode is provided in the V10 application section.

Note: RSN and RSP must be grounded in V10 mode.

#### OVER/UNDERVOLTAGE SHUTDOWN/RETRY BIT

The Over/Undervoltage Shutdown/Retry bit allows the user to select the global over and undervoltage fault strategy for all the outputs. In an overvoltage or undervoltage condition on the VPWR pin, all outputs are commanded OFF. The Over/Undervoltage control bit sets the operation of the outputs when returning from over/under voltage. Setting the Over/Undervoltage bit to logic [1] forces all outputs to remain OFF when  $V_{PWR}$  returns to normal level. To turn the output ON again, the corresponding input pin or SPI bit must be reactivated. Setting the Over/Undervoltage bit to logic [0] commands all outputs to resume their previous state when  $V_{PWR}$  returns to normal level. Table 7. below provides the output state when returning from over or undervoltage.

GINx DINx Input Pin	SPI Bit	Over/ Undervoltage Control Bit	OUTEN Input pin	State When Returning From Over/Undervoltage		
Х	Х	X	1	OFF		
Х	Х	1	0	OFF		
0	0	0*	0	OFF		
Х	1	0*	0	ON		
1	Х	0*	0	ON		

Table 7. Overvoltage/Undervoltage Truth Table

Note: The SPI bit does not control the Gate Driver outputs in the Ignition mode, only in the GPGD mode.

An undervoltage condition on  $V_{DD}$  results in the global shutdown of all outputs and reset of all internal control registers. The  $V_{DD}$  undervoltage threshold is between 0.8 V and 2.8 V

### **PWM<sub>x</sub> ENABLE BIT**

Gate Driver outputs programmed as GPGDs may be used as low frequency PWM outputs. The PWM generators are enabled via bits 0 through 3 in the Mode Select command. Bits 0 through 3 correspond to outputs GD0 through GD3, respectively. Once the frequency and duty cycle are programmed through the PWM Frequency & DC command, the PWM output may be turned ON and OFF through the PWM enable bit. Further information on PWM control is provided in the GPGD mode section of this data sheet.

<sup>\*</sup> Default setting



#### **IGNITION (IGBT) GATE DRIVER MODE**

The MC33810 contains dedicated circuitry necessary for automotive ignition control systems. Each gate driver may be individually configured as an Ignition Gate Driver with the following features:

- · Spark duration signal
- · Open secondary timer
- Soft shutdown control
- · Low-voltage flyback clamp
- · Ignition ignition coil current measurement
- · MAXI output and control
- NOMI output
- · Maximum dwell timer

In the Ignition Mode, several control strategies are in place to control the IGBT for enhanced system performance. Information acquired from the FBx pin allows the device to produce a Spark Duration signal output (SPKDUR) and detect open secondary ignition coils. Based on the FBx signal and Spark Command register settings, the device performs the appropriate gate control (Low-voltage Flyback Clamp, Soft Shutdown) and produces the SPKDUR output.

The FBx pin is connected to the collector of the IGBT through an external 9:1 resistor divider network. The recommended values for the resistor divider network is 36 k and 4.02 k, with the 36 k resistor connected from the IGBT collector to the FBx pin and the 4.02 K resistor connected from the FBx pin to ground.

Additional controls to the gate driver are achieved by sensing the current through the external IGBT. The Resistor Sense Positive (RSP) and Resistor Sense Negative (RSN) inputs are use to measure the voltage across an external 20 m $\Omega$  or 40 m $\Omega$  current sense resistor. A gain select bit in the Spark Command SPI Command messages should be set to a logic [1] (gain of 2) when using a 20 m $\Omega$  current sense resistor. When using a 40 m $\Omega$  current sense resistor, the gain select bit should be set to a logic [0] (gain of 1 is the default value).

The ignition coil current is compared with the output of the DACs which have been programmed via the SPI Commands. The comparison generates the Nominal Current signal (NOMI) and the Maximum Current signal (MAXI). Both signals have a low output when the ignition coil current is below the programmed DAC value and a high output when the current is above the programmed DAC value.

When the GDx output is shutdown because of the control strategy, the output may be activated again by toggling the input control.

#### **SPARK COMMAND**

The Spark Command is an Ignition mode command used to program the parameters for the Ignition mode features listed below:

- · End spark threshold (EndSparkTh bits)
- Open secondary fault timer (OSFLT bits)
- · Secondary clamp (secondary clamp bit)
- · Soft shutdown enable (SoftShutDn bit)
- · Ignition ignition coil current amplifier gain (Gain Sel bit)
- Overlapping dwell disable (Overlap Dwell Disable bit)
- · Maximum dwell enable (MaxDwellEn bit)
- · Maximum dwell timer (MaxDwellTimer bits)
- · End of spark filter timer value

Spark Command address and data bits are listed in Table 21

NOTE: Gate driver outputs programmed to be GPGDs are not affected by the Spark commands.

#### **SPARK DURATION SIGNAL**

The Spark Duration is defined as the beginning of current flow to the end of current flow across the spark plug gap. Because the extremely high-voltage ignition coil secondary output is difficult to monitor, corresponding lower voltage signals generated on the ignition coil primary are often used. The FBx pins monitor the ignition coil primary voltage (IGBT Collector) through a 10 to 1 voltage divider. When the IGBT is disabled, the rise in the FBx signal indicates a sparkout condition is occurring at the spark plug gap.

The device considers the initial thresholds for spark duration to be  $V_{IH} = V_{PWR} + 21 \text{ V}$  for rising edge as measured on the collector of the IGBT. The spark duration falling edge reference is programmable via SPI through the End Spark Threshold bits 0 and 1 (See <u>Table 8</u>).

Figure 5 illustrates a typical ignition event with Dwell Time and Spark Duration indicated.



**Channel 1: GINx IGBT Gate Drive Channel 2: IGBT Collector Voltage** 

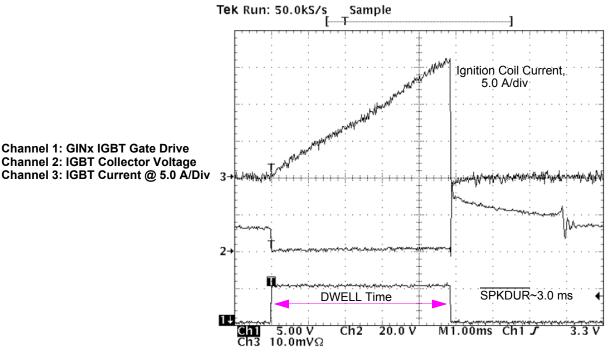


Figure 6. Ignition Coil Charge and Spark Event

 $V_{PWR}$  = 16.0 V

Default settings

Begin spark threshold V<sub>IH</sub> = V<sub>PWR</sub> + 21 V

End spark threshold  $V_{IL} = V_{PWR} + 5.5 V$ 

The pulse width of the SPKDUR signal is measured by the MCU timer/input capture port to determine the actual spark duration. Spark Duration information is then used by the MCU spark control algorithm to optimize the Dwell Time.

Spark Command Bit<b1,b0> **End Spark Threshold (VIL) VPWR + 2.75** 00 01 **VPWR + 5.5** 10 **VPWR + 8.2 VPWR + 11.0** 11

Table 8. End Spark Threshold

#### **OPEN SECONDARY TIMER**

A fault due to open in the ignition coil secondary circuit can be determined by waveforms established on the ignition coil primary during a spark event. The spark event is initiated by the turn OFF of the IGBT. The voltage on the collector of the IGBT rises up to the IGBT's internal collector to gate clamp voltage (typically 400 volts). Collector to gate clamp events normally last 5.0 µs to 50 µs. In an open ignition coil secondary fault condition, the collector to gate clamp event lasts much longer. The oscilloscope waveform in Figure 7 and Figure 8 compares a normal spark signature with an open secondary fault condition signature.



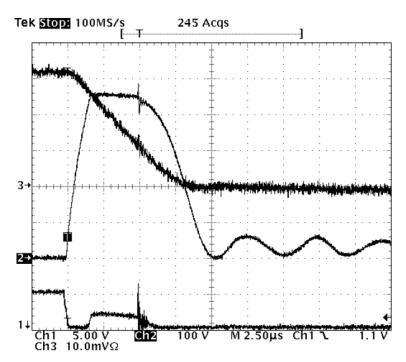


Figure 7. Normal Spark Event

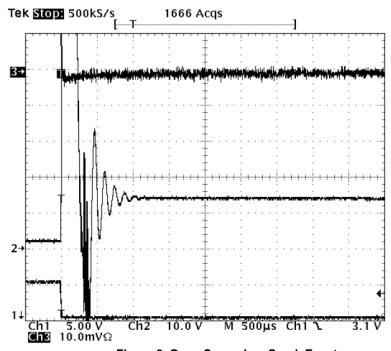


Figure 8. Open Secondary Spark Event

The Open Secondary timer is initiated on the rising edge of the ignition coil primary spark signal and terminated on the falling edge. The rising edge Open Secondary threshold is  $V_{IL}$  = 135 V at primary, no hysteresis. The falling edge Open Secondary threshold is  $V_{IL}$  = 135 V.

Collector to gate clamp durations lasting longer than the selected Open Secondary Fault Time interval (<u>Table 9</u>) indicate a failed spark event. When the Open Secondary Fault Time is exceeded and the low-voltage clamp is enabled, the GDx output activates the low-voltage clamp shown in <u>Figure 9</u>. The Logic for this low-voltage clamp is defined in <u>Figure 9</u>



Table 9. Open Secondary Timer

Spark Command Bits <b3,b2></b3,b2>	Open Secondary Fault Timer OSFLT (μs)
00	10
01	20
10	50
11	100

#### **LOW-VOLTAGE CLAMP**

The low-voltage clamp is an internal clamp circuit which biases the IGBT's gate voltage in order to control the collector to emitter voltage to V<sub>PWR</sub> +11 V. This technique is used to dissipate the energy stored in the ignition coil over a longer period of time than if the internal IGBT clamp were used.

In the Open Secondary Fault condition, all of the stored energy in the ignition coil is dissipated by the IGBT. This fault condition requires the use of a higher energy rated IGBT than would otherwise be needed. The low-voltage clamp spreads out the energy dissipation over a longer period of time, thus allowing the use of a lower energy rated IGBTs. The internal low-voltage clamp is connected between the IGBT's collector (through an external resistor) and the IGBT's gate. The energy stored in the ignition coil is dissipated by the IGBT, not the internal clamp. The internal clamp only provides the bias to the IGBT.

Several logical signals are required as inputs to activate the GDx Low-voltage Clamp feature. The GDx Low-voltage Clamp feature may be disabled through bit 4 of the Spark Command message.

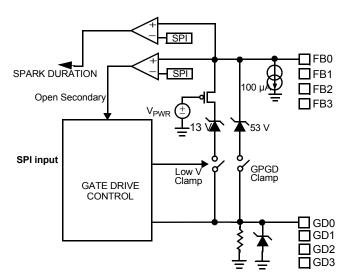


Figure 9. Low-voltage Clamp



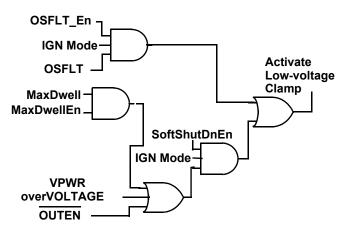


Figure 10. Low-voltage Clamp Logic

#### SOFT SHUTDOWN ENABLE

The Soft Shutdown feature is enabled via the SPI by asserting control bit 5 in the Spark Command message. When enabled, the following events initiate a soft shutdown control of the gate driver.

- OUTEN = High (Outputs Disabled)
- · Overvoltage on VPWR pin
- · Max dwell time

Soft shutdown is designed to prevent an ignition spark while turning off the external IGBT. The low-voltage clamp is activated to provide the mechanism for a soft shutdown.

#### **GAIN SELECT BIT**

The ignition coil current comparators are used to compare the programmed NOMI and MAXI DAC value with voltage across the external current sense resistor. When selecting a gain of two, the ignition coil current sense resistor must be reduced from 40 m $\Omega$  to 20 m $\Omega$ .

# **OVERLAPPING DWELL ENABLE BIT**

Overlapping dwell occurs when two or more Ignition mode drivers are commanded ON at the same time. In this condition with the Overlapping Dwell Bit enabled, the MAXI DAC threshold value is increased as a percentage of the nominal programmed value. The percent increase is determined by bit 5 through bit 7 of the DAC Command.

Table 10. Overlapping Dwell Compensation	Table 10.	Overlapping	Dwell Com	pensation
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DAC Command Bits <b7,b6,b5></b7,b6,b5>	Overlap Compensation (%)
000	0%
001	7%
010	15%
011	24%
100	35% (default)
101	47%
110	63%
111	80%

#### **MAXIMUM DWELL ENABLE BIT**

Bit 8, the Maximum Dwell Enable bit, allows the user to enable the Maximum Dwell Gate Turnoff feature. When the Max Dwell bit is programmed as logic 0 (disabled), the device does not perform a low-voltage clamp due to Max Dwell (See Figure ).



# MAXIMUM DWELL GATE TURN OFF FEATURE

In automotive ignition systems, dwell time is defined as the duration of time an ignition coil is allowed to charge. The 33810 starts the measure of time from the gate drive ON command. If the dwell time is greater than the Max Dwell Timer setting (<u>Table 11</u>), the offending ignition gate driver is commanded OFF. The Max Dwell Gate Turn OFF feature may be disabled via bit 8 of the Spark Command. When the feature is disabled, the Max Dwell fault bits are always logic 0. The Max Dwell Timer feature pertains to Ignition mode only and does not affect gate drivers configured as GPGDs.

The Max Dwell gate turn OFF signal is a logically ANDed with the Soft Shutdown bit to activate a Low-voltage Active Clamp (See Figure ).

**Table 11. Maximum Dwell Timer** 

Spark Command Bit <b11,b10,b9></b11,b10,b9>	MAX Dwell Timer MaxDwell (ms)
000	2
001	4
010	8
011	16
100	32 (default)
101	64
110	64
111	64

# DAC COMMAND (DIGITAL TO ANALOG CONVERSION COMMAND)

The DAC command is an Ignition mode command which sets the nominal ignition coil current (NOMI) and maximum ignition coil current (MAXI) DAC values. Bits 0 through 4 set the NOMI threshold value and bits 8 through 11 set the MAXI threshold values. The DAC command and default values are listed in the SPI Command Summary <u>Table 21</u>. The NOMI output is used by the MCU as a variable in dwell and spark control algorithms.

#### **NOMI DAC BITS**

The NOMI output signal is generated by comparing the external current sense resistor differential voltage (Resistor Sense Positive, Resistor Sense Negative) with the SPI programmed NOMI DAC value. When the NOMI event occurs, the NOMI output pin is asserted (high). The NOMI output is only a flag to the MCU and it's output does not affect the gate driver.

When using a  $20~\text{m}\Omega$  resistor as the current sense resistor, the gain select of the differential amplifier connected to RSP and RSN should be set to a gain of 2 via the SPI Command Message Spark command (Command 0100, hex 4), Control bit 6 =1. When using a  $40~\text{m}\Omega$  resistor as the current sense resistor, the gain select of the differential amplifier connected to RSP and RSN, should be set to a gain of 1 via the SPI Command Message Spark Command (Command 0100, hex 4), Control bit 6 = 0. This is also the default value. The NOMI output provides a means to alert the MCU when the ignition coil primary current equals the value programmed into the NOMI DAC.

In V10 mode, the NOMI pin is reconfigured as a MAXI input pin from a third MC33810 device in the system. In this mode, a NOMI input has effectively the same control as an internal MAXI signal. Further information is provided in the V10 mode application section of this data sheet.



**Table 12. Nominal Current DAC Select** 

DAC Command Bits<4,3,2,1,0>	NOMI Current (A)	Differential Voltage (mV) $R_S = 20 \text{ m}\Omega$ (Gain = 2)	Differential Voltage (mV) R <sub>S</sub> = 40 m $\Omega$ (Gain = 1)
00000	3.00	60	120
00001	3.25	65	130
00010	3.50	70	140
00011	3.75	75	150
00100	4.00	80	160
00101	4.25	85	170
00110	4.50	90	180
00111	4.75	95	190
01000	5.00	100	200
01001	5.25	105	210
01010	5.50	110	220
01011	5.75	115	230
01100	6.00	120	240
01101	6.25	125	250
01110	6.50	130	260
01111	6.75	135	270
10000	7.00	140	280
10001	7.25	145	290
10010	7.50	150	300
10011	7.75	155	310
10100	8.00	160	320
10101	8.25	165	330
10110	8.50	170	340
10111	8.75	175	350
11000	9.00	180	360
11001	9.25	185	370
11010	9.50	190	380
11011	9.75	195	390
11100	10.00	200	400
11101	10.25	205	410
11110	10.50	210	420
11111	10.75	215	430